



# SPP3413W

## P-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPP3413W is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

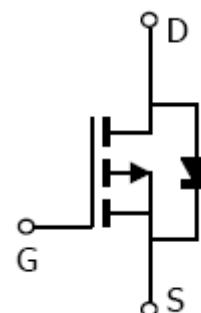
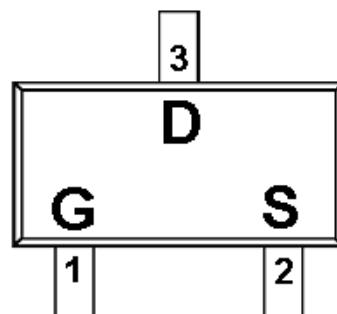
### FEATURES

- ◆ -20V/-3.4A,R<sub>DS(ON)</sub>=95mΩ@V<sub>GS</sub>=-4.5V
- ◆ -20V/-2.4A,R<sub>DS(ON)</sub>=120mΩ@V<sub>GS</sub>=-2.5V
- ◆ -20V/-1.7A,R<sub>DS(ON)</sub>=145mΩ@V<sub>GS</sub>=-1.8V
- ◆ Super high density cell design for extremely low R<sub>DS</sub> (ON)
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-23 package design

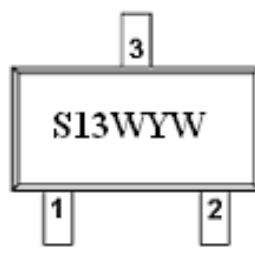
### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION(SOT-23)



### PART MARKING





# SPP3413W

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### PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPP3413WS23RGB	SOT-23	S13W

※ Week Code : A ~ Z( 1 ~ 26 ) ; a ~ z( 27 ~ 52 )

※ SPP3413WS23RGB : Tape Reel ; Pb – Free ; Halogen – Free

### ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate –Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current(T <sub>J</sub> =150°C)	TA=25°C	-3.5	A
	TA=70°C	-2.8	
Pulsed Drain Current	I <sub>DM</sub>	-15	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-1.4	A
Power Dissipation	TA=25°C	1.25	W
	TA=70°C	0.8	
Operating Junction Temperature	T <sub>J</sub>	-55/150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	105	°C/W



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### ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

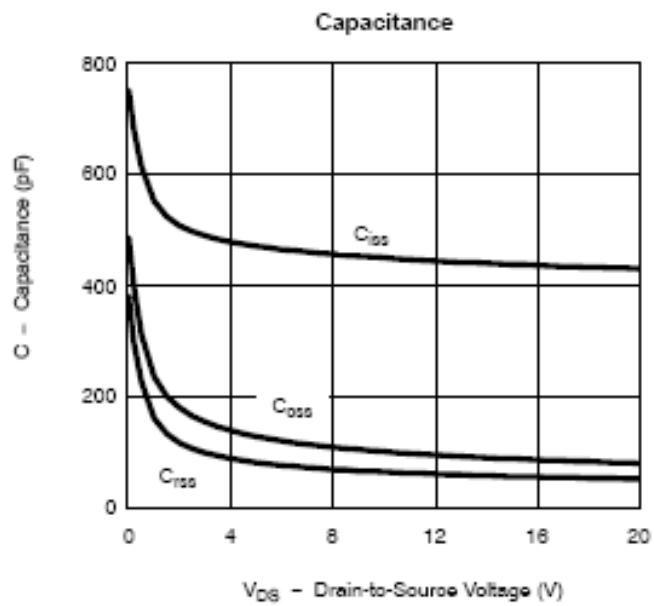
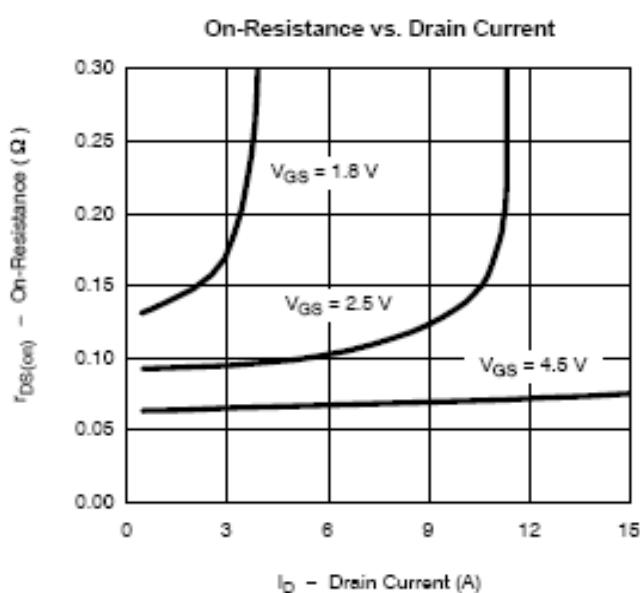
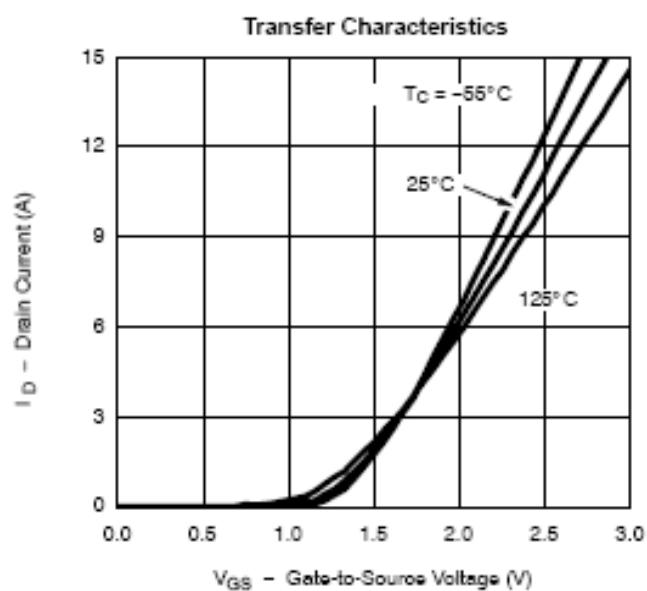
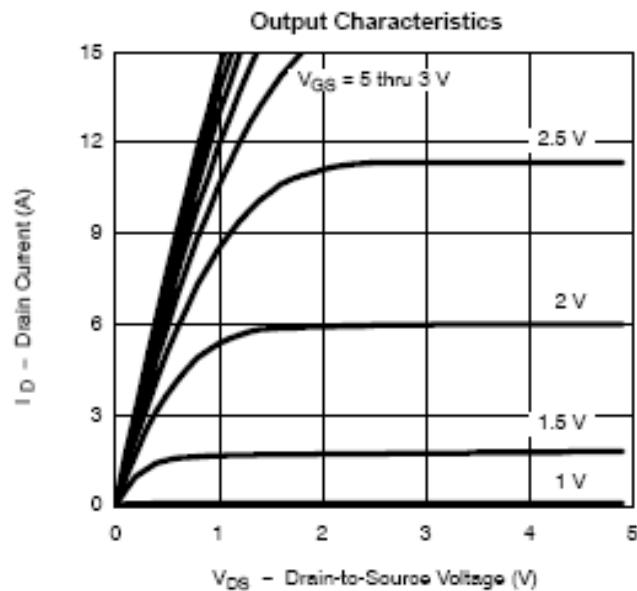
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, ID=-250uA	-20			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , ID=-250uA	-0.35		-0.8	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	
		V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-5	uA
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≤-5V, V <sub>GS</sub> =-4.5V	-6			A
Drain-Source On-Resistance	R <sub>DSS(on)</sub>	V <sub>GS</sub> =-4.5V, ID=-3.4A		0.076	0.095	
		V <sub>GS</sub> =-2.5V, ID=-2.4A		0.097	0.120	
		V <sub>GS</sub> =-1.8V, ID=-1.7A		0.123	0.145	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =-5V, ID=-2.8A		6		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.5A, V <sub>GS</sub> =0V		-0.8	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-6V, V <sub>GS</sub> =-4.5V ID=-2.8A		4.8	8	
Gate-Source Charge	Q <sub>gs</sub>			1.0		nC
Gate-Drain Charge	Q <sub>gd</sub>			1.0		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-6V, V <sub>GS</sub> =0V f=1MHz		485		
Output Capacitance	C <sub>oss</sub>			85		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			40		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-6V, R <sub>L</sub> =6Ω ID=-1.0A, V <sub>GEN</sub> =-4.5V R <sub>G</sub> =6Ω		10	16	
	t <sub>r</sub>			13	23	
Turn-Off Time	t <sub>d(off)</sub>			18	25	
	t <sub>f</sub>			15	20	nS



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### TYPICAL CHARACTERISTICS

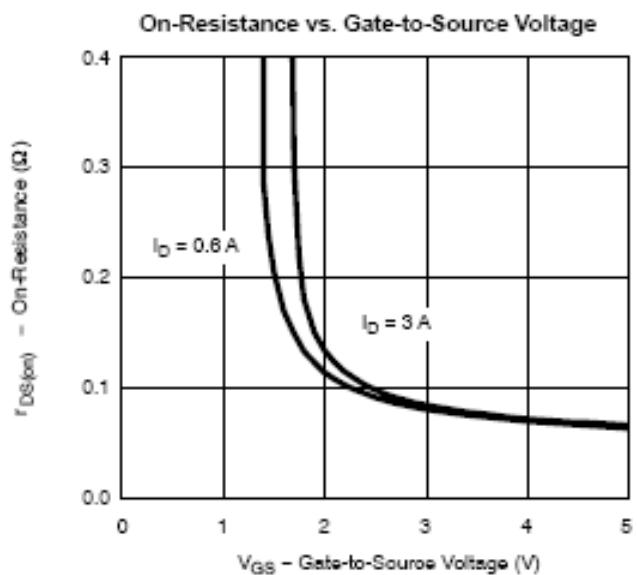
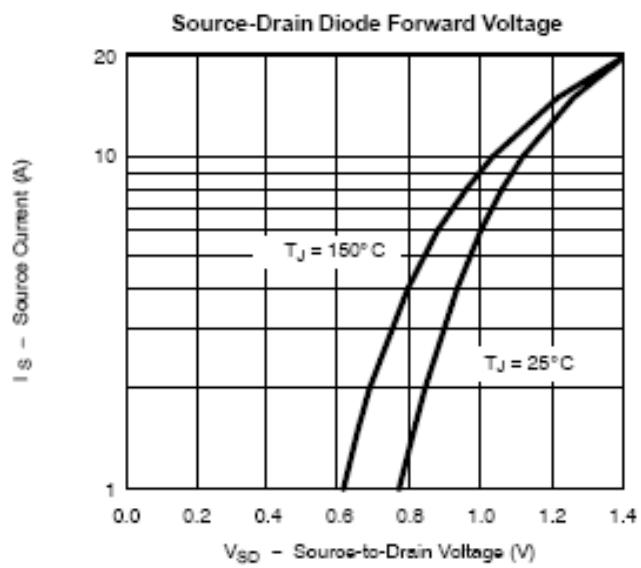
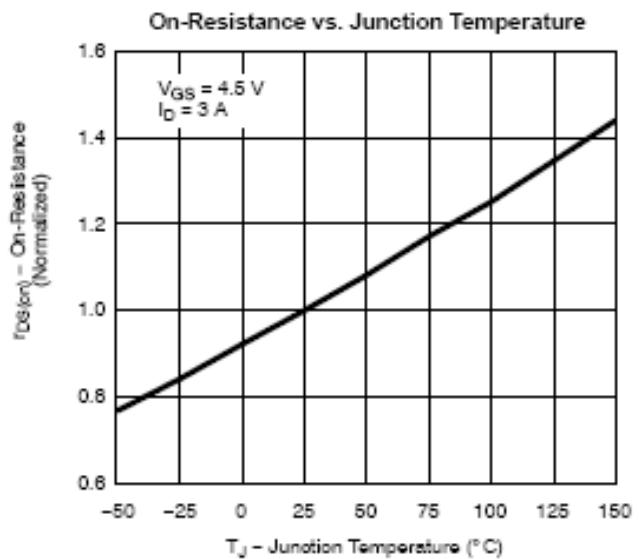
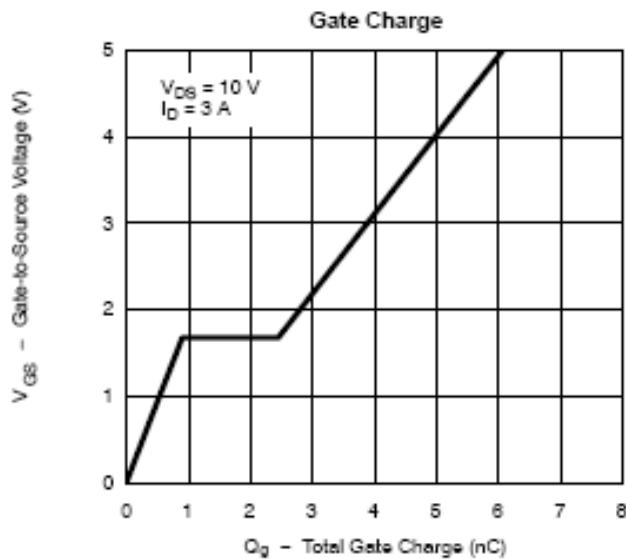




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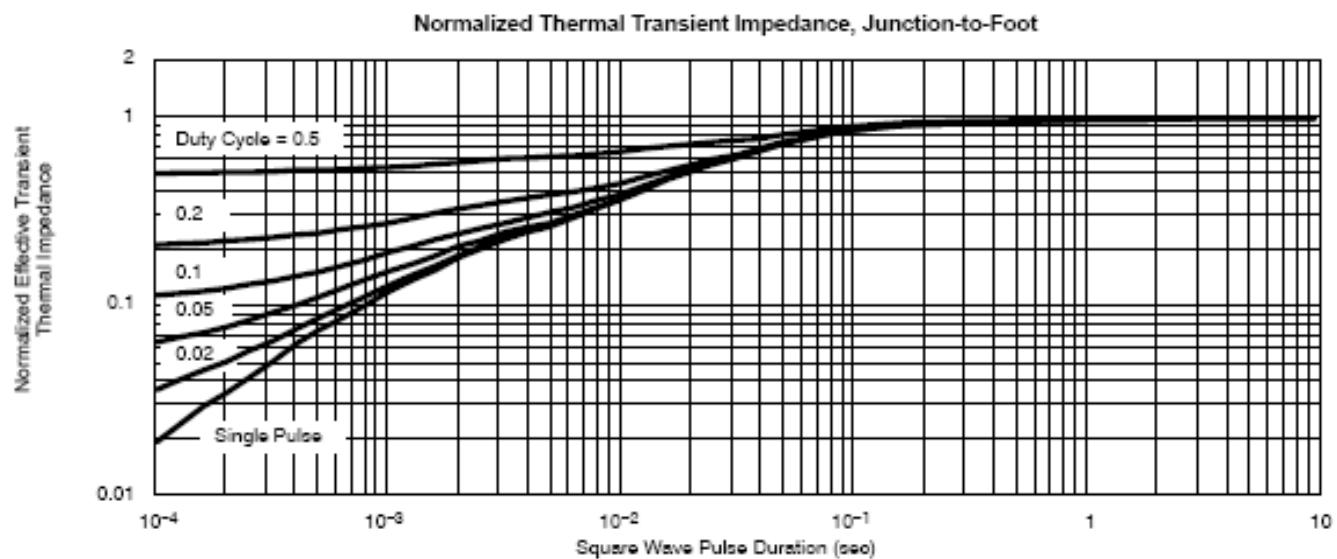
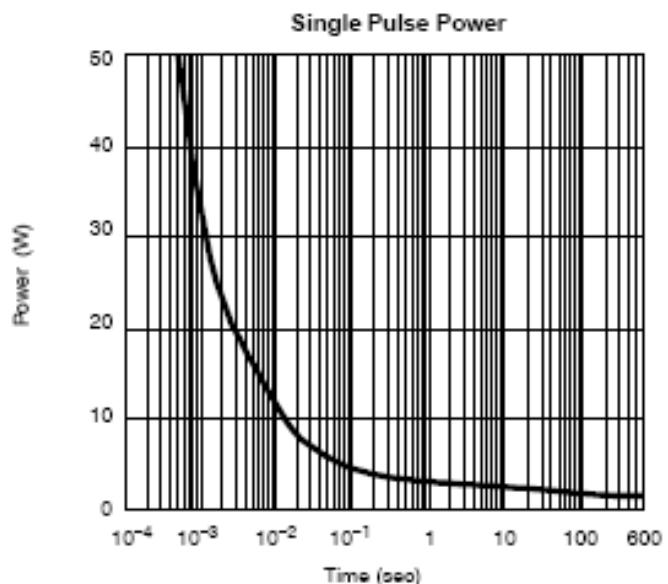
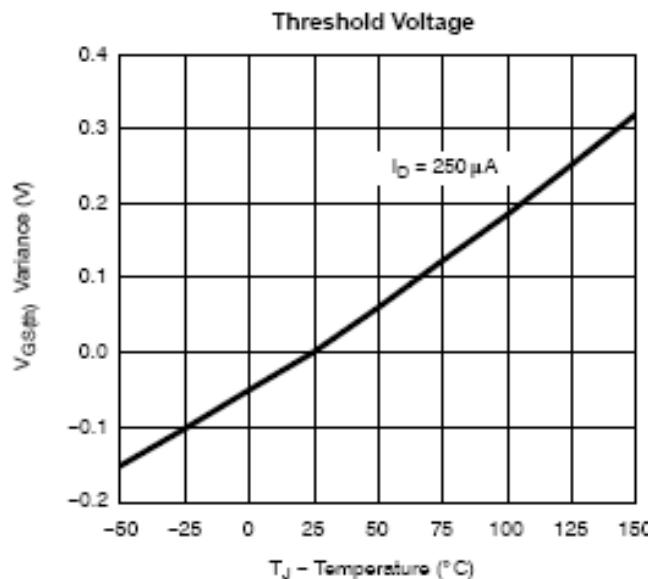




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### TYPICAL CHARACTERISTICS





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